Docket No.

241433US2S

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshiaki ASAO

SERIAL NO: NEW APPLICATION

GAU: HEREWITH

FOR: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

### **INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

FILED:

Applicant(s) wish to disclose the following information.

#### REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

#### RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

#### CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

### DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment form is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

**EXAMINER:** 

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

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# **STATEMENT OF RELEVANCY**

# **Reference AW on Form PTO-1449:**

This publication is referred to in the specification. See page 1, line 23.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241433US2S		SERIAL NO. NEW APPLICATION		
LIST OF REFERENCES CITED BY APPLICANT				Yoshiaki ASAO				
				FILING DATE HEREWITH		GROUP		
EXAMINER		DOCUMENT	T 54.75	NAA45	CLASS	SUB	FILING DATE	
INITIAL		NUMBER	DATE	NAME	CLASS	CLASS	IF APPROPRIATE	
	AA	5,734,605	3/31/98	Xiaodong T. ZHU, et al.				
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	AR AS AT AU AV	Roy SCHEUERLEIN	et al. "A 10NS	READ AND WRITE NON-VOLATILE	MEMORY AF	RRAY USIN	NG A MAGNETIC rs, February 8, 2000, pg.	
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Examiner	AR AS AT AU AV  AW AX	Roy SCHEUERLEIN TUNNEL JUNCTION	et al. "A 10NS	READ AND WRITE NON-VOLATILE	MEMORY AF	RRAY USIN	rs, February 8, 2000, pg.	